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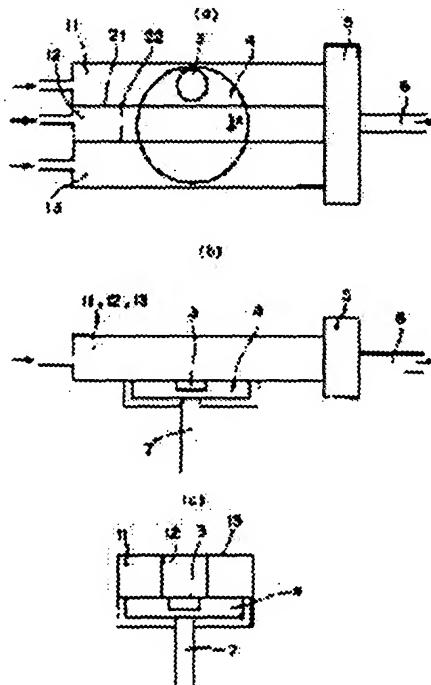
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(54) THIN FILM FORMING METHOD AND DEVICE

(57)Abstract:

PURPOSE: To provide an epitaxial growth method and a vapor growth device through which it is carried out, wherein an atomic growth layer of high quality is grown at a high speed.

CONSTITUTION: Material gases different from each other in content are supplied through gas flow paths 11 and 13 provided inside a reaction oven to form the flows of gases. A substrate 3 is so set as to be movable in parallel with the direction of a gas flow on the same plane with the inner walls of the gas flow paths 11 and 13. A first process wherein the surface of the substrate 3 is introduced into the flow path 11, brought into contact with a flow of gas, and made to adsorb elements contained in it and a second process wherein the surface of the substrate 3 is introduced into the flow path 13, brought into contact with a flow of gas, and made to react on elements contained in it to form an atomic layer thin film are provided, whereby an atomic layer is made to grow through a chemical vapor growth method.



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